



# Thyristor Module

$V_{RRM} = 2 \times 1800 \text{ V}$

$I_{TAV} = 49 \text{ A}$

$V_T = 1.34 \text{ V}$

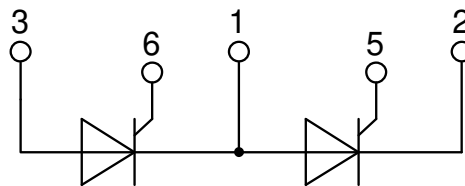
Phase leg

Part number

**MCC44-18io8B**



Backside: isolated



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

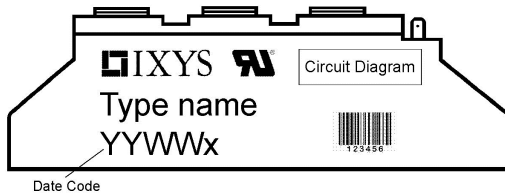
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| Thyristor      |  |  | Ratings                   |      |      |                   |
|----------------|--|--|---------------------------|------|------|-------------------|
| Symbol         | Definition   | Conditions   | min.                      | typ. | max. | Unit              |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$   |                           |      | 1900 | V                 |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}C$   |                           |      | 1800 | V                 |
| $I_{RD}$       | reverse current, drain current                       | $V_{R/D} = 1800 V$   | $T_{VJ} = 25^{\circ}C$    |      | 100  | $\mu A$           |
|                |  | $V_{R/D} = 1800 V$   | $T_{VJ} = 125^{\circ}C$   |      | 5    | mA                |
| $V_T$          | forward voltage drop                                 | $I_T = 100 A$  | $T_{VJ} = 25^{\circ}C$    |      | 1.34 | V                 |
|                |  | $I_T = 200 A$  |                           |      | 1.75 | V                 |
|                |  | $I_T = 100 A$  | $T_{VJ} = 125^{\circ}C$   |      | 1.34 | V                 |
|                |  | $I_T = 200 A$  |                           |      | 1.80 | V                 |
| $I_{TAV}$      | average forward current                              | $T_C = 85^{\circ}C$  | $T_{VJ} = 125^{\circ}C$   |      | 49   | A                 |
| $I_{T(RMS)}$   | RMS forward current                                  | 180° sine  |                           |      | 77   | A                 |
| $V_{T0}$       | threshold voltage                                    | } for power loss calculation only  | $T_{VJ} = 125^{\circ}C$   |      | 0.85 | V                 |
| $r_T$          | slope resistance                                     |  |                           |      | 3.7  | m $\Omega$        |
| $R_{thJC}$     | thermal resistance junction to case                  |  |                           |      | 0.53 | K/W               |
| $R_{thCH}$     | thermal resistance case to heatsink                  |  |                           | 0.2  |      | K/W               |
| $P_{tot}$      | total power dissipation                              |  | $T_C = 25^{\circ}C$       |      | 180  | W                 |
| $I_{TSM}$      | max. forward surge current                           | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 45^{\circ}C$    |      | 1.15 | kA                |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |      | 1.24 | kA                |
|                |  | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 125^{\circ}C$   |      | 980  | A                 |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |      | 1.06 | kA                |
| $I^2t$         | value for fusing                                     | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 45^{\circ}C$    |      | 6.62 | kA <sup>2</sup> s |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |      | 6.40 | kA <sup>2</sup> s |
|                |  | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 125^{\circ}C$   |      | 4.80 | kA <sup>2</sup> s |
|                |  | t = 8,3 ms; (60 Hz), sine  | $V_R = 0 V$               |      | 4.63 | kA <sup>2</sup> s |
| $C_J$          | junction capacitance                                 | $V_R = 400 V$ f = 1 MHz  | $T_{VJ} = 25^{\circ}C$    |      | 54   | pF                |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30 \mu s$   | $T_C = 125^{\circ}C$      |      | 10   | W                 |
|                |  | $t_p = 300 \mu s$  |                           |      | 5    | W                 |
| $P_{GAV}$      | average gate power dissipation                       |  |                           |      | 0.5  | W                 |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 125^{\circ}C$ ; f = 50 Hz  | repetitive, $I_T = 150 A$ |      | 150  | A/ $\mu s$        |
|                |  | $t_p = 200 \mu s$ ; $di_G/dt = 0.45 A/\mu s$ ;<br>$I_G = 0.45 A$ ; $V = \frac{2}{3} V_{DRM}$                             | non-repet., $I_T = 49 A$  |      | 500  | A/ $\mu s$        |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)  | $T_{VJ} = 125^{\circ}C$   |      | 1000 | V/ $\mu s$        |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$    |      | 1.5  | V                 |
|                |  |  | $T_{VJ} = -40^{\circ}C$   |      | 1.6  | V                 |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$    |      | 100  | mA                |
|                |  |  | $T_{VJ} = -40^{\circ}C$   |      | 200  | mA                |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$  | $T_{VJ} = 125^{\circ}C$   |      | 0.2  | V                 |
| $I_{GD}$       | gate non-trigger current                             |  |                           |      | 10   | mA                |
| $I_L$          | latching current                                     | $t_p = 10 \mu s$   | $T_{VJ} = 25^{\circ}C$    |      | 450  | mA                |
|                |  | $I_G = 0.45 A$ ; $di_G/dt = 0.45 A/\mu s$  |                           |      |      |                   |
| $I_H$          | holding current                                      | $V_D = 6 V$ $R_{GK} = \infty$  | $T_{VJ} = 25^{\circ}C$    |      | 200  | mA                |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$<br>$I_G = 0.45 A$ ; $di_G/dt = 0.45 A/\mu s$   | $T_{VJ} = 25^{\circ}C$    |      | 2    | $\mu s$           |
| $t_q$          | turn-off time  | $V_R = 100 V$ ; $I_T = 150 A$ ; $V = \frac{2}{3} V_{DRM}$<br>$di/dt = 10 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$ | $T_{VJ} = 100^{\circ}C$   |      | 150  | $\mu s$           |



| Package TO-240AA |  |                      |                                     | Ratings |      |      |  |
|------------------|--|----------------------|-------------------------------------|---------|------|------|--|
| Symbol           | Definition   | Conditions           | min.                                | typ.    | max. | Unit |  |
| $I_{RMS}$        | RMS current  | per terminal         |                                     |         | 200  | A    |  |
| $T_{VJ}$         | virtual junction temperature                                 |                      | -40                                 |         | 125  | °C   |  |
| $T_{op}$         | operation temperature  |                      | -40                                 |         | 100  | °C   |  |
| $T_{stg}$        | storage temperature  |                      | -40                                 |         | 125  | °C   |  |
| <b>Weight</b>    |  |                      |                                     |         | 81   | g    |  |
| $M_D$            | mounting torque  |                      | 2.5                                 |         | 4    | Nm   |  |
| $M_T$            | terminal torque  |                      | 2.5                                 |         | 4    | Nm   |  |
| $d_{Spp/App}$    | creepage distance on surface   striking distance through air | terminal to terminal | 13.0                                | 9.7     |      | mm   |  |
| $d_{Spb/Apb}$    |  | terminal to backside | 16.0                                | 16.0    |      | mm   |  |
| $V_{ISOL}$       | isolation voltage  | t = 1 second         |                                     | 4800    |      | V    |  |
|                  |  | t = 1 minute         | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 4000    |      | V    |  |



| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCC44-18io8B    | MCC44-18io8B       | Box           | 36       | 454532   |

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 125^{\circ}\text{C}$

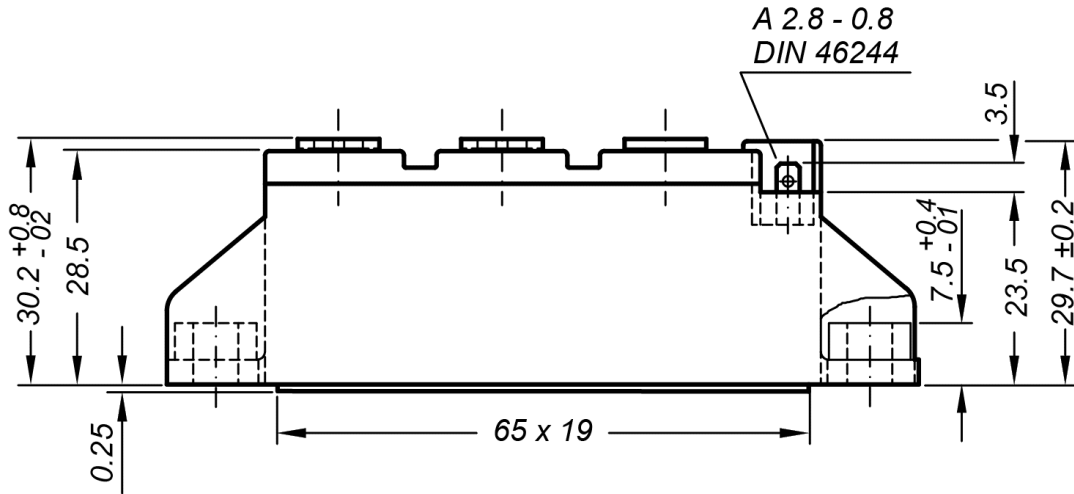


**Thyristor**

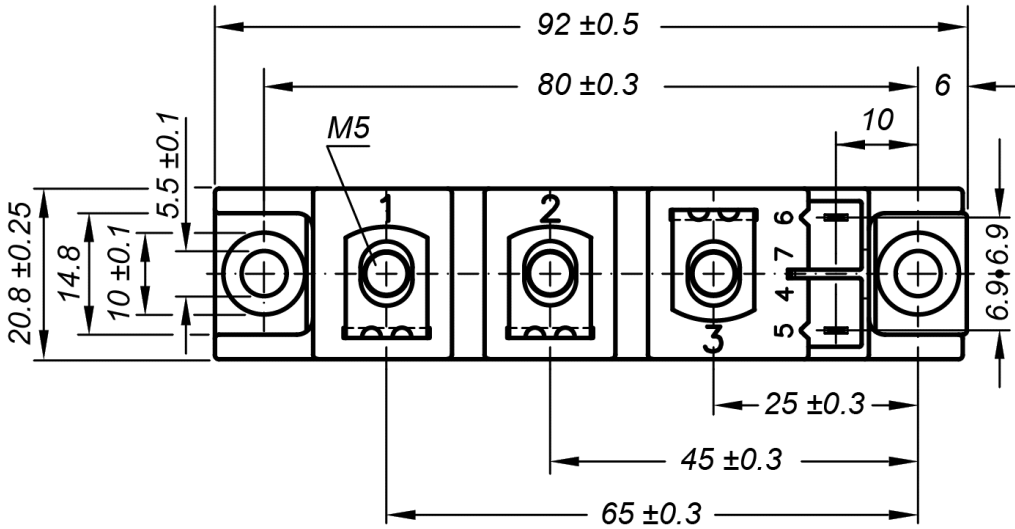
|              |                    |      |    |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage  | 0.85 | V  |
| $R_{0\ max}$ | slope resistance * | 4.1  | mΩ |



**Outlines TO-240AA**



General tolerance: DIN ISO 2768 class „c“

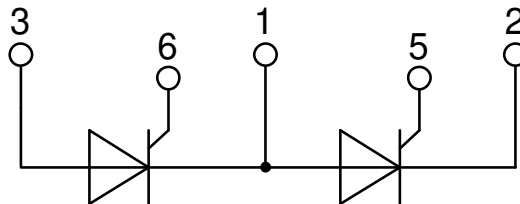


**Optional accessories for modules**

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 200L (L = Left for pin pair 4/5)

Type ZY 200R (R = Right for pin pair 6/7) } UL 758, style 3751



**Thyristor**

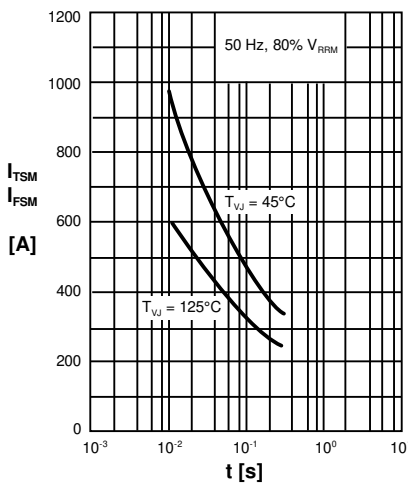


Fig. 1 Surge overload current  
 $I_{TSM}$ ,  $I_{FSM}$ : Crest value,  $t$ : duration

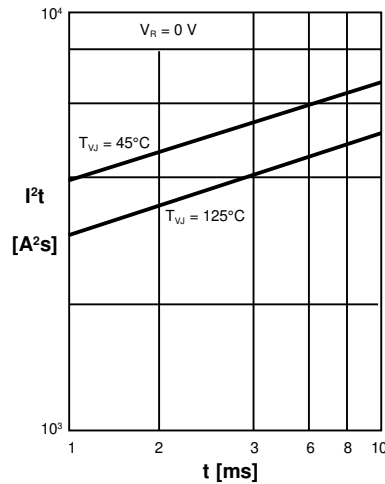


Fig. 2  $I^2t$  versus time (1-10 ms)

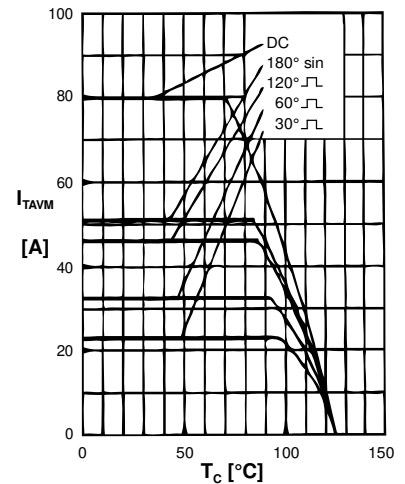


Fig. 3 Maximum forward current at case temperature



Fig. 4 Power dissipation vs. onstate current and ambient temperature (per thyristor/diode)

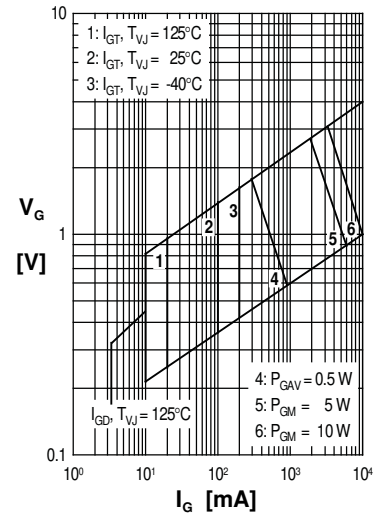


Fig. 5 Gate trigger characteristics



Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature



Fig. 7 Gate trigger delay time

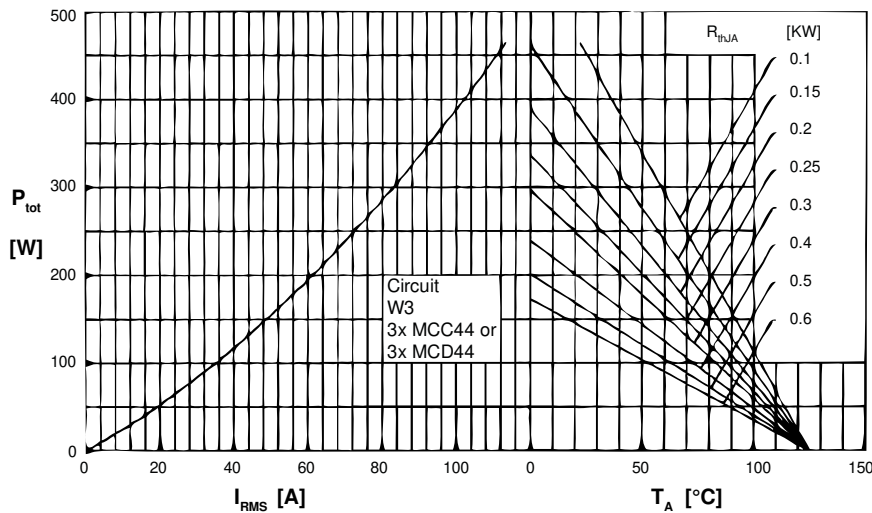
**Thyristor**


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

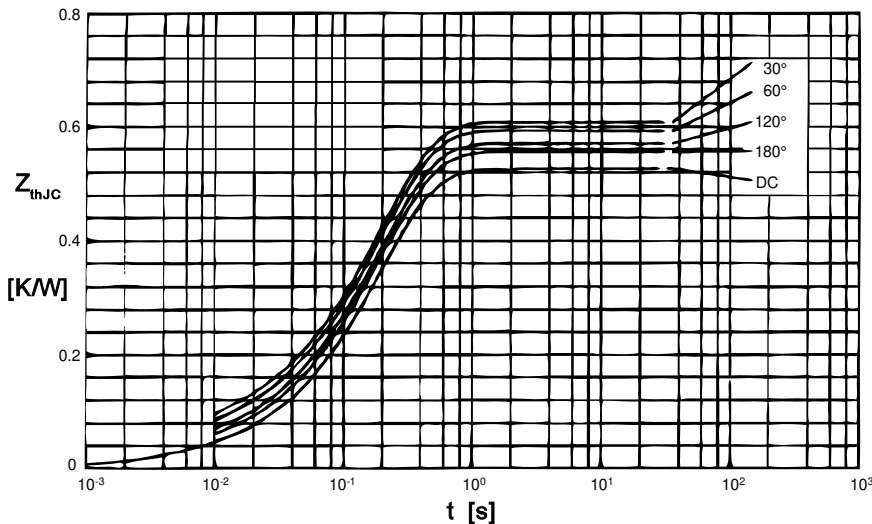


Fig. 9 Transient thermal impedance junction to case (per thyristor)

 $R_{thJC}$  for various conduction angles d:

| d    | $R_{thJC}$ [KW] |
|------|-----------------|
| DC   | 0.53            |
| 180° | 0.55            |
| 120° | 0.58            |
| 60°  | 0.60            |
| 30°  | 0.62            |

 Constants for  $Z_{thJC}$  calculation:

| i | $R_{thi}$ [KW] | $t_i$ [s] |
|---|----------------|-----------|
| 1 | 0.015          | 0.0035    |
| 2 | 0.026          | 0.0200    |
| 3 | 0.489          | 0.1950    |

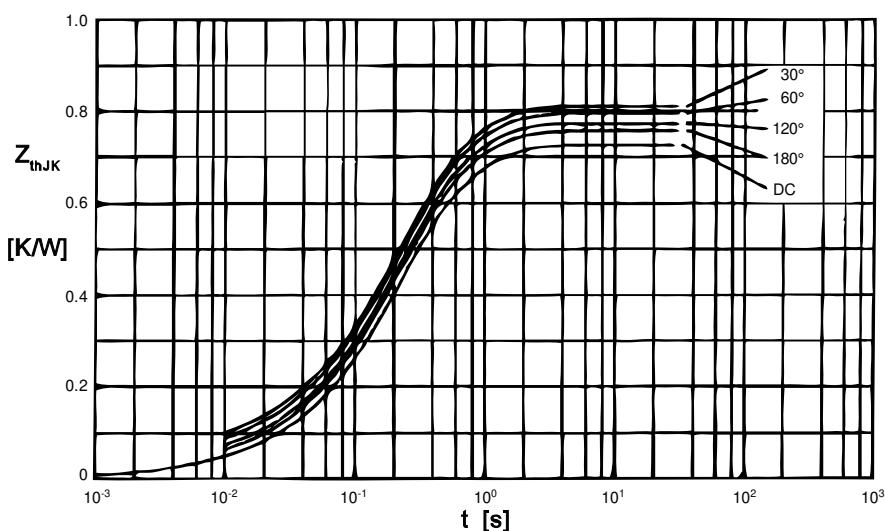


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

 $R_{thJK}$  for various conduction angles d:

| d    | $R_{thJK}$ [KW] |
|------|-----------------|
| DC   | 0.73            |
| 180° | 0.75            |
| 120° | 0.78            |
| 60°  | 0.80            |
| 30°  | 0.82            |

 Constants for  $Z_{thJK}$  calculation:

| i | $R_{thi}$ [KW] | $t_i$ [s] |
|---|----------------|-----------|
| 1 | 0.015          | 0.0035    |
| 2 | 0.026          | 0.0200    |
| 3 | 0.489          | 0.0195    |
| 4 | 0.200          | 0.6800    |

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